Supplementary data

Triptycene Derivatives as High-T_g Host Materials for Various Electrophosphorescent Devices†

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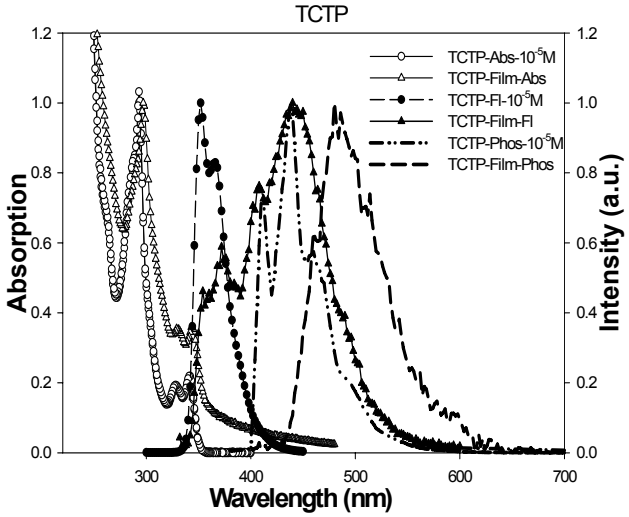

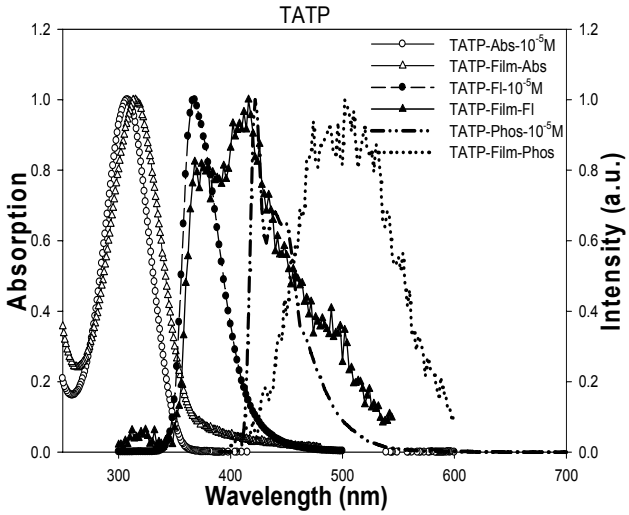

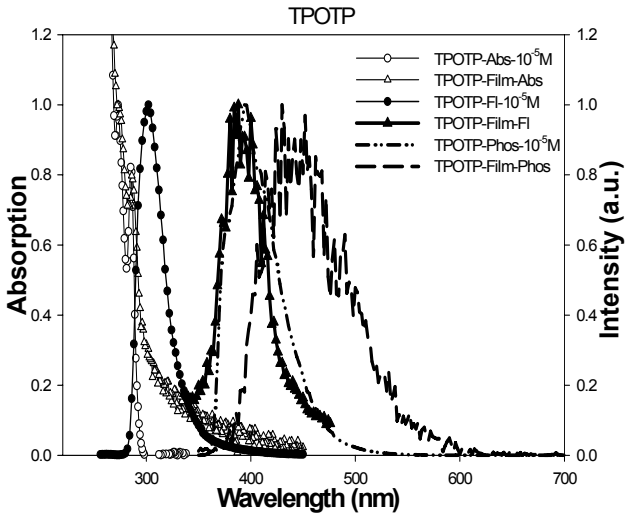

Fig. S1. The UV-vis absorption and fluorescence (room temperature) and phosphorescence thin film spectra (77 K) of TCTP, TATP and TPOTP with thickness of 300 nm (red lines); the corresponding solution spectra were also recorded for comparison (blue lines).

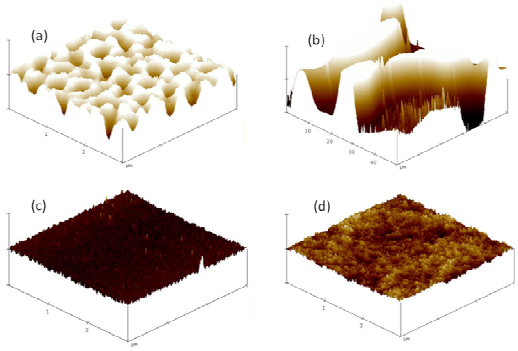

Fig. S2. Surface morphology of *m*CP and TPOTP doped with 6% FIrpic by AFM. (a) *m*CP without annealing, (b) *m*CP after annealing at 120 ℃ under nitrogen for 15 h, (c) TPOTP without annealing, and (d) TPOTP after annealing at 120 ℃ under nitrogen for 15 h (the rms roughness value of (a), (b), (c), and (d) are 1.755, 29.574, 0.340, 0.383, respectively).